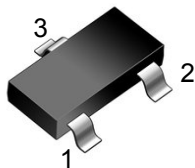
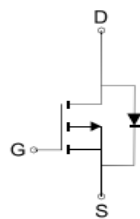




SOT-23



MARKING: A1SHB



P-Channel MOSFET

Features

Advanced trench process technology
 High density cell design for Ultra Low On-Resistance
 Halogen free and RoHS compliant

Mechanical Data

SOT-23 Small Outline Plastic Package
 EpoxyUL:94V-0

Summary of Packing Options

Package	Packing Description	Packing Quantity	Industry Standard
SOT-23	Tape/Reel,7" reel	3000	EIA-481-1

Maximum Ratings & Thermal Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified.)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	-20	V	
Gate-Source Voltage	V_{GS}	±12		
Continuous Drain Current	I_D	-4.1	A	
Pulsed Drain Current ¹⁾	I_{DM}	-15		
Maximum Power Dissipation ²⁾	P_D	TA = 25°	1.25	W
		TA = 75°C	0.8	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150	°C	
Junction-to-Ambient Thermal Resistance (PCB mounted) ²⁾	R_{thJA}	100		°C/W
Junction-to-Ambient Thermal Resistance (PCB mounted) ³⁾		166		

Notes

- 1) Pulse width limited by maximum junction temperature.
- 2) Surface Mounted on FR4 Board, t ≤ 5 sec.
- 3) Surface Mounted on FR4 Board.

Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified).

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Drain-Source On-State Resistance ¹⁾	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -4.1A$		46	52	mΩ
		$V_{GS} = -2.5V, I_D = -3.0A$		60	75	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	0.4		1	V
Zero Gate Voltage Drain Current I_{D0}	I_{DSS}	$V_{DS} = -20V, V_{GS} = 0V$			-1	μA
		$V_{DS} = -20V, V_{GS} = 0V, T_J = 55°C$			-10	
Gate Body Leakage	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0V$			±100	nA
Forward Transconductance ¹⁾	g_{fs}	$V_{DS} = -5V, I_D = -3.5A$		6.5	—	S



Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified).

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Dynamic						
Total Gate Charge	Q_g	$V_{DS} = -6V, I_D \cong -3.5A$ $V_{GS} = -4.5V$		5.8	10	nC
Gate-Source Charge	Q_{gs}			0.85		
Gate-Drain Charge	Q_{gd}			1.7		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -6V, R_L = 6\Omega$ $I_D \cong -1.1A, V_{GEN} = -4.5V$ $R_G = 6\Omega$		13	25	ns
Turn-On Rise Time	t_r			36	60	
Turn-Off Delay Time	$t_{d(off)}$			42	70	
Turn-Off Fall Time	t_f			34	60	
Input Capacitance	C_{iss}	$V_{DS} = -6V, V_{GS} = 0V$ $f = 1.0\text{ MHz}$		415		pF
Output Capacitance	C_{oss}			223		
Reverse Transfer Capacitance	C_{rss}			87		
Source-Drain Diode						
Max. Diode Forward Current	I_S				-1.6	A
Diode Forward Voltage	V_{SD}	$I_S = -1.6A, V_{GS} = 0V$		-0.8	-1.2	V

1) Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

Ratings and Characteristic Curves

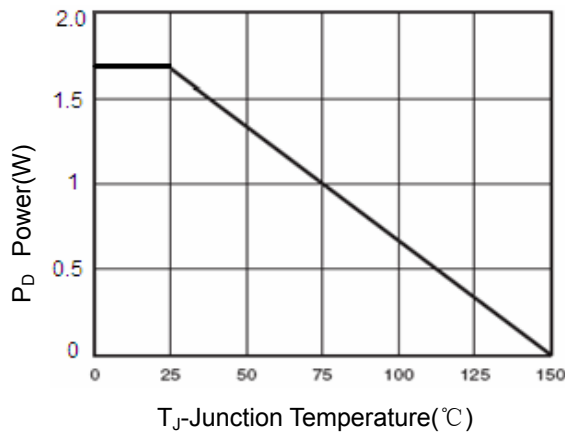


Figure 1 Power Dissipation

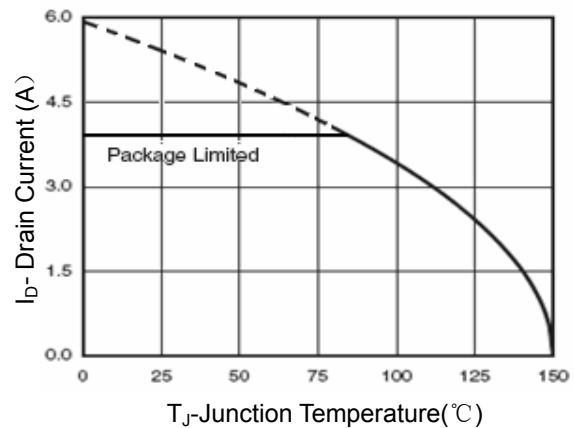


Figure 2 Drain Current

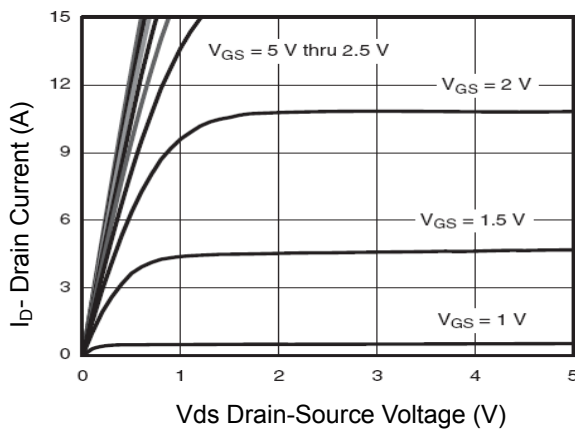


Figure 3 Output Characteristics

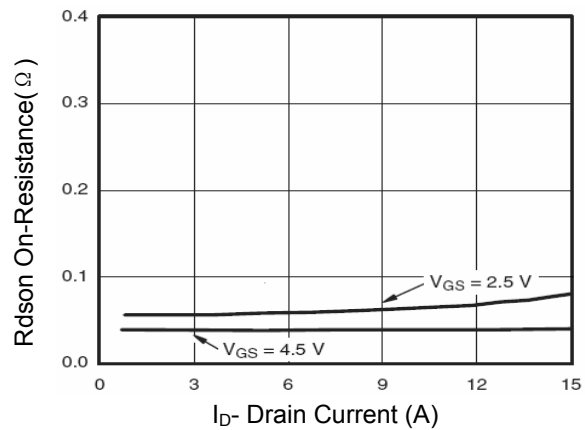


Figure 4 Drain-Source On-Resistance

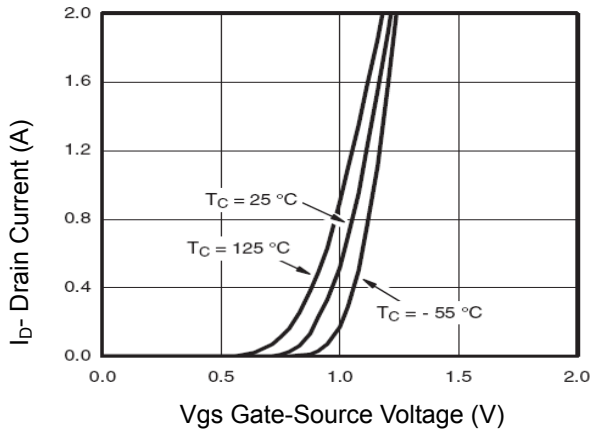


Figure 5 Transfer Characteristics

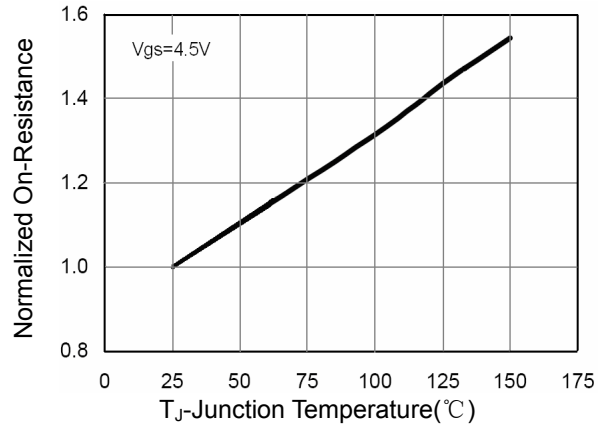


Figure 6 Drain-Source On-Resistance

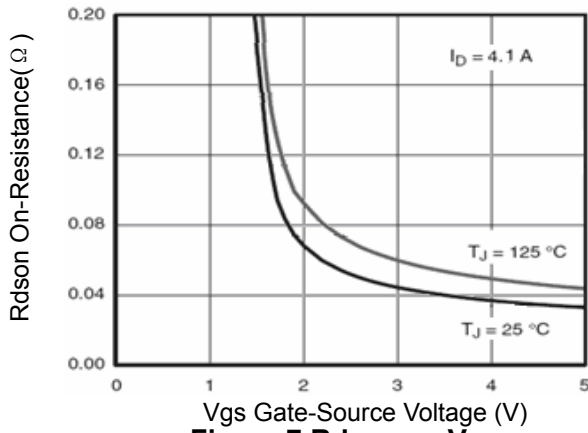


Figure 7 $R_{DS(on)}$ vs V_{GS}

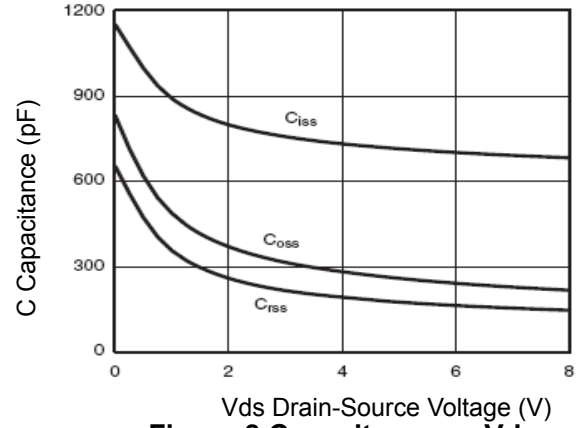


Figure 8 Capacitance vs V_{DS}

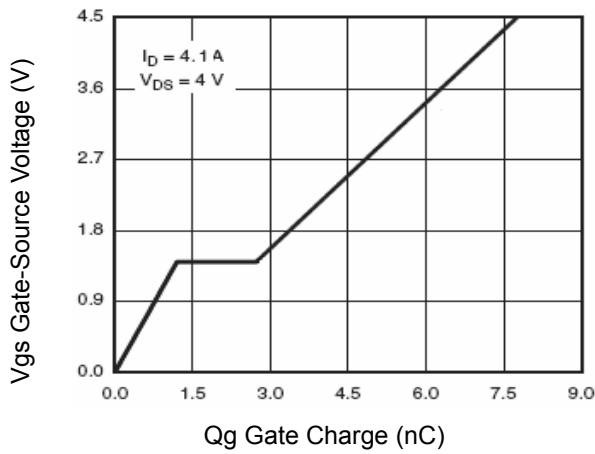


Figure 9 Gate Charge

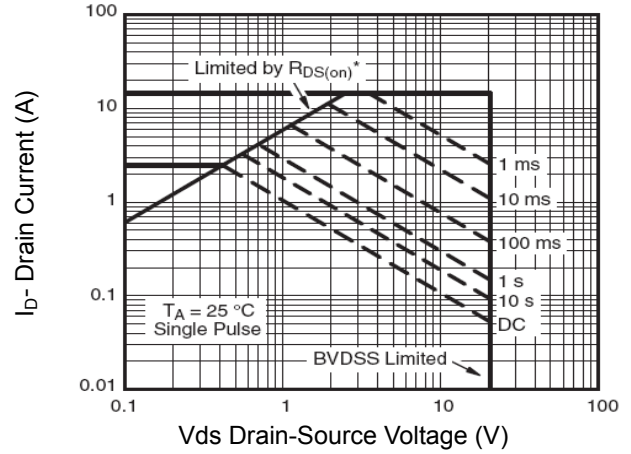
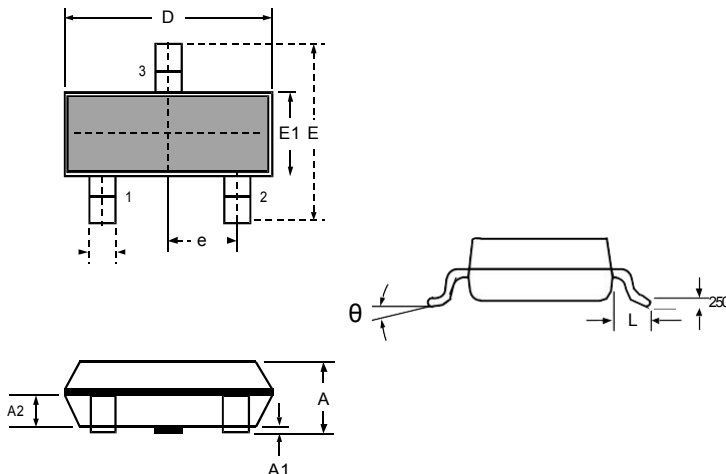


Figure 10 Safe Operation Area

Package Outline Dimensions: SOT-23



DIMENSIONS

SYMBOL	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
D	2.800	3.000	0.110	0.118
b	0.300	0.500	0.012	0.020
E	2.250	2.550	0.089	0.100
E1	1.200	1.400	0.047	0.055
e	0.950 BSC		0.037 BSC	
L	0.300	0.500	0.012	0.020
θ	0	8°	0	8°